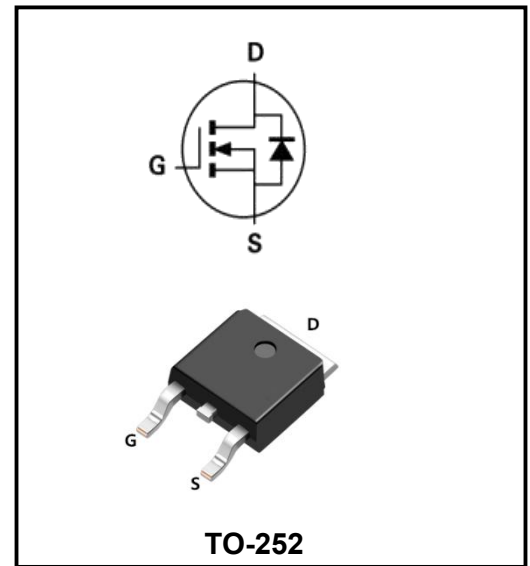


60V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	80A
V_{DSS}	60V
R_{DS(on)-typ}(@V_{GS}=10V)	< 12mΩ (Type: 9 mΩ)



APPLICATIONS

- ◆ Load switch
- ◆ PWM Application
- ◆ Power Management

Case: Molded plastic

- ◆ Mounting Position: Any
- ◆ Molded Plastic: UL Flammability Classification Rating 94V-0
- ◆ Lead free in compliance with EU RoHS 2011/65/EU directive
- ◆ Solder bath temperature 275°C maximum, 10s per JESD 22-B106

Product Specification Classification

Part Number	Package	Marking	Pack
YFW80N06AD	TO-252	YFW 80N06AD XXXXX	2500PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

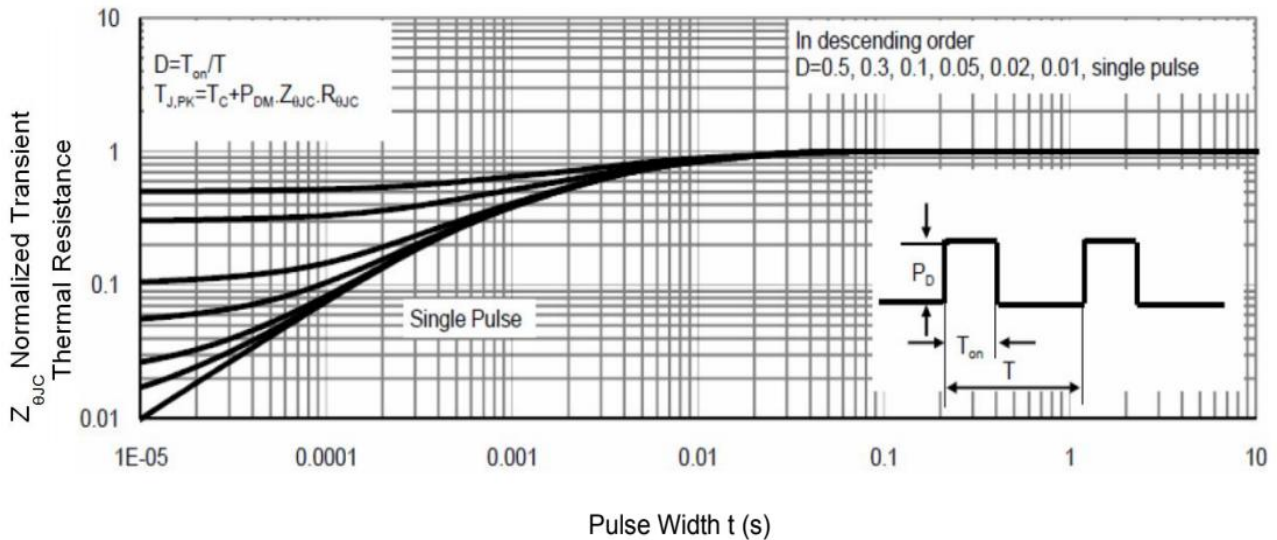
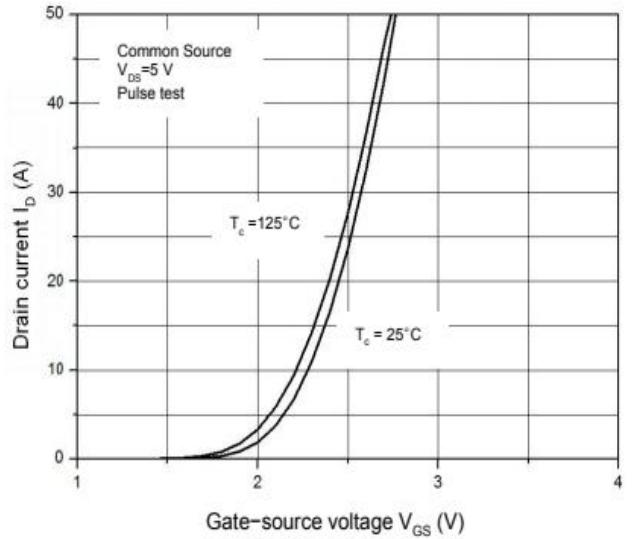
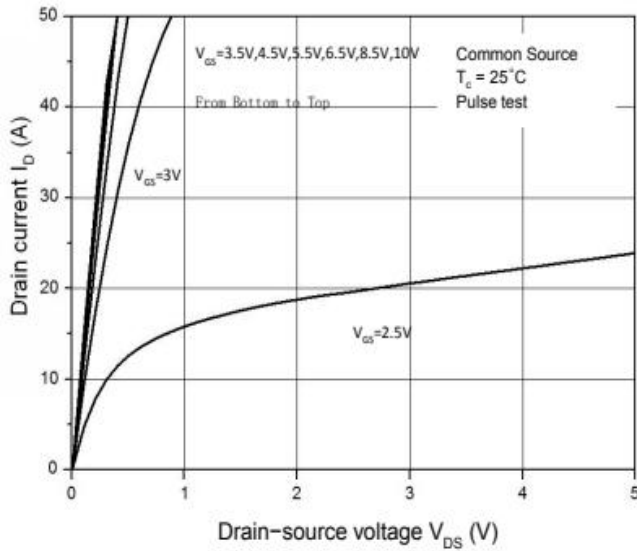
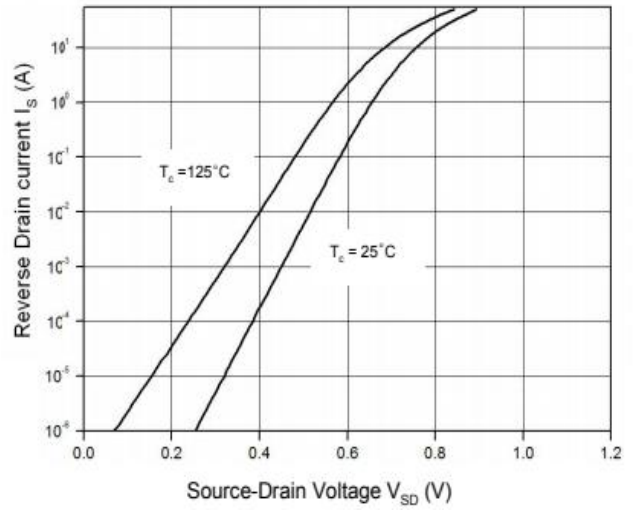
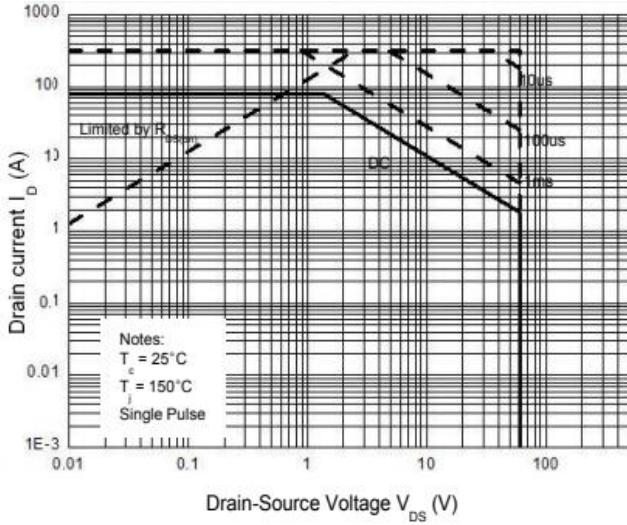
Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	60	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous drain current	I_D	80	A
Pulsed Drain Current (Note1)	I_{DM}	320	A
Power dissipation	P_D	110	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	140	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +175	°C
Thermal Resistance Junction-Case	R_{θJC}	2.1	°C/W
Thermal Resistance, Junction to Ambient	R_{θJA}	62	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current	V _{DS} =60V, V _{GS} = 0 V	I_{DSS}	-	-	1	μA
Gate Leakage Current	V _{GS} = ± 20 V, V _{DS} = 0 V	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	V_{GS(th)}	2	-	4	V
Drain-source on-state resistance	V _{GS} =10V, I _D =30A	R_{DS(ON)}	-	9	12	mΩ
Forward Transconductance	V _{DS} = 5 V, I _D = 10 A	g_{fs}	10	-	-	S
Input Capacitance	V _{GS} =0V V _{DS} =15V f=1MHz	C_{iss}	-	3750	-	pF
Output Capacitance		C_{oss}	-	269	-	
Reverse Transfer Capacitance		C_{rss}	-	255	-	
Turn-on delay time(Note2)	V _{GS} =10V V _{DD} =30V R _G =2Ω I _D =30A	t_{d(on)}	-	18	-	ns
Rise Time(Note2)		T_r	-	170	-	
Turn-Off Delay Time(Note2)		t_{d(OFF)}	-	464	-	
Fall Time(Note2)		t_f	-	140	-	
Total Gate Charge(Note2)	I _D =30A V _{DS} =30V V _{GS} =10V	Q_g	-	12	-	nC
Gate to Source Charge(Note2)		Q_{gs}	-	13	-	
Gate-Drain Charge(Note2)		Q_{gd}	-	68	-	
Maximun Body-Diode Continuous Current		I_S	-	-	80	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	320	A
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =1A, T _J =25°C	V_{SD}	-	-	1.2	V

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

Ratings and Characteristic Curves



Package Outline Dimensions Millimeters

TO-252

	Dim.	Min.	Max.
	A	2.1	2.5
	A1	6.3	6.9
	B	0.95	1.55
	B1	0.6	0.8
	B2	0.75	0.95
	C	Typ0.5	
	D	5.3	5.5
	D1	3.65	4.05
	E	5.8	6.4
	E1	Typ2.3	
	E2	Typ4.6	
	O	0	0.15
	L1	10	11
L2	Typ1.5		
L3	0.7	1	
All Dimensions in millimeter			

单击下面可查看定价，库存，交付和生命周期等信息

[>>YFW\(佑风微\)](#)